

Ultrafast Rectifier

MURB1660CT

FEATURES

- Guarding for over voltage protection
- Dual rectifier construction, positive center tap
- Metal of silicon rectifier, majority carrier conduction
- Low forward voltage, high efficiency
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

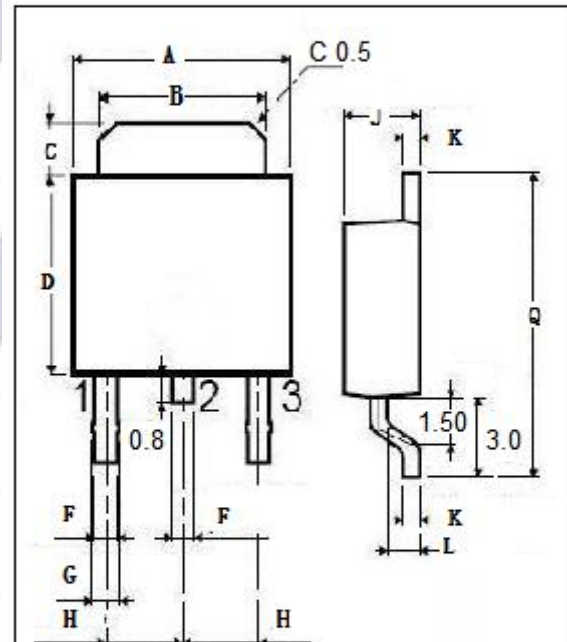
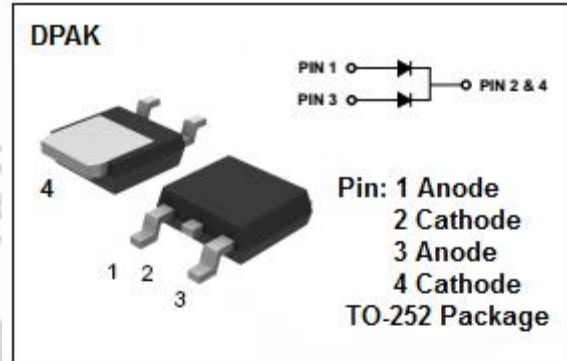
APPLICATIONS

- Switching power supply
- Power switching circuits

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ABSOLUTE MAXIMUM RATINGS (T<sub>a</sub>=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>R</sub> RM V <sub>R</sub> WM V <sub>R</sub>	Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	600	V
I <sub>F(AV)</sub>	Average Rectified Forward Current	16	A
I <sub>FSM</sub>	Nonrepetitive Peak Surge Current (Surge applied at rated load conditions half-wave, single phase, 60Hz)	100	A
P <sub>D</sub>	Maximum power dissipation	75	W
T <sub>J</sub>	Junction Temperature	-65~175	°C
T <sub>stg</sub>	Storage Temperature Range	-65~175	°C



DIM	mm	
	MIN	MAX
A	6.40	6.60
B	5.20	5.40
C	1.15	1.35
D	5.70	6.10
F	0.65	
G	0.75	
H	2.10	2.50
J	2.10	2.40
K	0.40	0.60
L	0.90	1.10
Q	9.90	10.1

## Fast Recovery Rectifier

## MURB1660CT

## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{thj-c}$	Thermal Resistance, Junction to Case	2.0	$^{\circ}\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS ( $T_a=25^{\circ}\text{C}$ ) (Pulse Test: Pulse Width=300  $\mu$  s, Duty Cycle  $\leq 2\%$ )

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
$V_F$	Maximum Instantaneous Forward Voltage	$I_F=8\text{A}; T_j=150^{\circ}\text{C}$ $I_F=8\text{A}; T_j=25^{\circ}\text{C}$	1.2 1.5	V
$I_R$	Maximum Instantaneous Reverse Current	$V_R=V_{RWM}$ $V_R=V_{RWM}; T_j=150^{\circ}\text{C}$	10 500	$\mu$ A
$t_{rr}$	Maximum Reverse Recovery Time	$I_F=0.5\text{A}; I_R=1\text{A}; I_{rr}=0.25\text{A}$	50	ns

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